AMENDMENTS TO THE CLAIMS

Pursuant to 37 C.F.R. § 1.121 the following listing of claims will replace all prior versions, and listings, of claims in the application.

1. (Previously Presented): A semiconductor device, comprising:

a semiconductor element with an area for a main surface of 1 mm^2 or greater;

a substrate having a thermal conductivity of 170 W/m-K or greater and having an upper surface on which said element is mounted and a bottom surface which is positioned on the opposite side; and

a ratio H/L being greater than or equal to 0.3 but less than 1.25, with L being the length in the long direction of a main surface of said semiconductor element, and H being the distance from a semiconductor element mounting part on said upper surface of said substrate to said bottom surface.

2. - 3. (Canceled)

4. (Previously Presented) The semiconductor device according to claim 1, further comprising:

a ratio of Y/L being equal to or greater than 2, with Y being the distance from one end of the bottom surface of the substrate to the opposite end of the bottom surface of the substrate along the same plane as L.

5. (Previously Presented) The semiconductor device according to claim 1, wherein the thermal conductivity of the substrate is equal to or greater than 200 W/m-K.

6. (Previously Presented) The semiconductor device according to claim 1, wherein the ratio H/L is greater than 0.45 but less than 1.25.

7. (Previously Presented) The semiconductor device according to claim 1, wherein the distance H is greater than or equal to 0.3 mm but less than or equal to 10 mm.

8. - 18. (Canceled).

19. (Previously Presented): A semiconductor device, comprising:

a semiconductor element with an area for a main surface of 1 mm^2 or greater;

a substrate having a thermal conductivity of 170 W/m-K or greater and having an upper surface on which the semiconductor element is mounted and a bottom surface which is positioned on the opposite side;

a metal layer formed on the upper surface of the substrate; and

a ratio H/L being greater than 0.3 but less than 1.25, with L being the length in the long direction of a main surface of said semiconductor element, and H being the distance from a semiconductor element mounting part on said upper surface of said substrate to said bottom surface.

20. (Previously Presented) The semiconductor device according to claim 19, wherein a maximum roughness Rmax of the metal layer is in a range of 0.1 to 20 micrometers.

21. (Previously Presented) The semiconductor device according to claim 19, further comprising:

a hole formed in the substrate;

a pin disposed within the hole that supplies power to the semiconductor element; and

an insulating material which fills a space between the inner surface of the hole and the pin.

22. (Previously Presented) The semiconductor device according to claim 19, further comprising:

a terminal plate that supplies power to the semiconductor element;

a connection member which connects between the substrate and the terminal plate.

23. - 25. (Canceled).